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Cora M. Utley
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of Christopher L. Chua

Group Art Unit: 2828

Application No.: 10/625,811

Examiner: Tuan N. Nguyen

Filed: July 23, 2003

Confirmation No.: 7775

For: PHASE ARRAY OXIDE-CONFINED VCSELs

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INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>			
JUL 31 2006 U.S. PATENT DOCUMENTS		APPLICANT(S) Christopher L. Chua	
		FILING DATE 7/23/2003	GROUP 2828

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